ANALOG DEVICES

8-Bit Low Cost Signal Conditioning ADC

AD670

1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/AD670

2.0 Part Number. The complete part number(s) of this specification follow: Part Number

Description

8-Bit Low Cost Signal Conditioning ADC

3.0 **Die Information**

Die Dimensions 3.1

AD670-000C

Die Size	Die Thickness mil	Bond Pad Metalization
111 mil x 174 mil	19 mil ± 2 mil	Al/Cu

3.2 Die Picture



1. D0 (LSB)

- 2. D1
- 3. D2
- 4. D3
- 5. D4
- 6. D5
- 7. D6
- 8. D7 (MSB)
- 9. STATUS
- 10. POWER GROUND
- 11. BPO/UPO*
- 12. FORMAT
- 13. R/W*
- 14. CE*
- 15. CS*
- 16. -VIN HI
- 17. -VIN LOW
- 18. +VIN HI
- 19. +VIN LOW
- 20. +VCC

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* = Active Low

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3.3 Absolute Maximum Ratings <u>1/</u>

V _{CC} to Ground	. 0V to +7.5V
Digital Inputs (Pin 11 – 15)	-0.5V to V _{CC} +0.5V
Digital Outputs (Pin 1 – 9)	. Momentary Short to V _{CC} or ground
Analog Inputs (Pin 16 – 19)	±30V
Storage Temperature Range	65°C to +150°C
Junction Temperature (T _J)	+150C
Operating Temperature Range	55°C to +125°C
Absolute Maximum Ratings Notes:	

1./ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

4.0 <u>Die Qualification</u>

In accordance with class-K version of Mil-Prf-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Samples Size and Qual Acceptance Criteria 25/2
- (b) Qual Sample Package DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I -Dice Electrical Characteristics							
Parameter	Symbol	Conditions <u>1</u> /	Limit Min	Limit Max	Units		
Relative Accuracy	RA	<u>2</u> /		±0.5	LSB		
Differential Nonlinearity	DNL	<u>3/4</u> /	8		Bits		
Gain Error	AE	2/		±1.5	LSB		
Unipolar Offset Error	OE	0V to +2.55V input range FS		±1	LSB		
Bipolar Offset Error	BOE	-1.28V to +1.27V FS		±1	LSB		
Power Supply Current	v Current I _{cc} VCC = 5.5V (DB0-DB7, R/W - High); (STATUS, CE, CS, FORMAT, BPO, UPO - LOW)			45	mA		
Digital Input High Voltage	VIH	<u>4</u> /	2		V		
Digital Input Low Voltage	VIL	<u>4</u> /		0.8	V		
Digital Input High Current	Iн	V _{IH} = 5V <u>4</u> /		100	μΑ		
Digital Input Low Current	l _{IL}	$V_{IL} = 0V \underline{4}/$	-100		μA		
Digital Output Low Voltage	Vol	$I_{OL} = 1.6 mA$, $V_{CC} = 5.5 V$		0.4	V		
Digital Output High Voltage	Vон	I _{он} = 0.5mA, V _{CC} = 4.5V	2.4		V		
Three-State Leakage Current	loz	Vapplied = 0V and 5V <u>4</u> /		±40	μΑ		
Conversion Time	Tc			10	μs		

Table I Notes:

 $\underline{1}/V_{CC}$ = +5V, T_A = 25°C, unless otherwise specified.

 $\underline{2}/$ Tested on both 2.55V full scale and -1.28V to 1.27V full scale.

 $\underline{3}$ / Minimum resolution for which there are no missing codes.

<u>4</u>/ Parameter is tested at V_{CC} = +5V, but is guaranteed from V_{CC} = 4.5V to V_{CC} = 5.5V.

Table II -Electrical Characteristics for Qual Samples							
Parameter	Symbol	Conditions <u>1</u> /	Sub- groups	Limit Min	Limit Max	Units	
Relative Accuracy	RΔ	2/	1		±0.5	I SB	
neithive needlacy	103		2, 3		±1	LJD	
Differential Nonlinearity	DNL	<u>3</u> /, <u>4</u> /	1, 2, 3	8		Bits	
Gain Error	٨	2/	1		±1.5	LSB	
Gain Litter	Λ _E	<u>Z</u> /	2, 3		±2.5		
Lipipolar Officat Error	0-	0V to +2.55V	1		±1	LSB	
	OF.	input range FS	2, 3		±2		
Pipelar Offcat Error			1		±1		
Bipolai Onset Error	BOE	-1.200 10 +1.270 F3	2, 3		±2	LDR	
Power Supply Current	lcc	VCC = 5.5V (DB0-DB7, R/W - High); (STATUS, CE, CS, FORMAT, BPO, UPO - LOW)	1, 2, 3		45	mA	
Digital Input High Voltage	VIH	<u>4</u> /	1, 2, 3	2		V	
Digital Input Low Voltage	VII	A/	1		0.8	V	
	VIL	<u>4</u> /	2, 3		0.7	v	
Digital Input High Current	IIH	V _{IH} = 5V <u>4</u> /	1, 2, 3		100	μΑ	
Digital Input Low Current	Ι _{ΙL}	$V_{IL} = 0V \underline{4}/$	1, 2, 3	-100		μΑ	
Digital Output Low Voltage	Vol	$I_{OL} = 1.6mA, V_{CC} = 5.5V$	1, 2, 3		0.4	V	
Digital Output High Voltage	Vон	I _{он} = 0.5mA, V _{cc} = 4.5V	1, 2, 3	2.4		V	
Three-State Leakage Current <u>4</u> /	loz	Vapplied = 0V and 5V	1, 2, 3		±40	μΑ	

Table II Notes:

 $\frac{1}{2}/V_{CC} = +5V, \text{ unless otherwise specified.}$ $\frac{2}{2}/\text{ Tested on both 2.55V full scale and -1.28V to 1.27V full scale.}$ $\frac{3}{2}/\text{ Minimum resolution for which there are no missing codes.}$ $\frac{4}{2}/\text{ Parameter is tested at V_{CC} = +5V, but is guaranteed from V_{CC} = 4.5V to V_{CC} = 5.5V.}$

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Table III - Life Test Endpoint and Delta Parameter (Product is tested in accordance with Table II with the following exceptions)								
Parameter	Symbol	Sub- groups	Post Burn In Limit		Post Life Test Limit		Life	Unite
			Min	Max	Min	Max	Delta	Units
Power Supply Current	lcc	1		50		55	±5	- mA
		2, 3				55		
Digital Output High Voltage	Vон	1	2.4		2.4		±.2	v
		2, 3			2.4			
Digital Output Low Voltage	V _{OL}	1		0.4		0.4	±.1	V
		2, 3				0.4		

5.0 Life Test/Burn-In Information

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

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Kev	Description of Change	Date
А	Initiate	20-DEC-01
В	Correct typo's on table III. VOH is 2.4V minimum. Remove \pm from endpoint limits.	27-Mar-02
С	Update web address. Make revision letter same on all pages	4-Mar-03
D	Update 1.0 Scope description	11-Jul-07
E	Update header/footer & add to 1.0 Scope Description.	19-Feb-08
F	Add Junction Temperature (T _J)+150°C to 3.3 Absolute Maximum Ratings	March 31, 2008
G	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	6-JUN-2009
Н	Updated fonts and sizes to ADI standards	22-Sep-2011

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